

# BCR10FM-12LC

600V - 10A - Triac

Medium Power Use

R07DS1409EJ0101

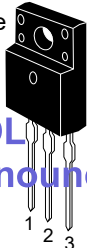
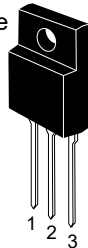
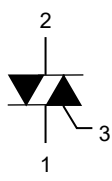
Rev.1.01

Feb. 19, 2019

## Features

- $I_T (RMS)$  : 10 A
- $V_{DRM}$  : 600 V
- $T_j$ : 150°C
- $I_{FGT1}$ ,  $I_{RGT1}$ ,  $I_{RGT III}$ : 50 mA
- Insulated Type
- Planar Passivation Type
- Viso: 2000 V

## Outline

<p>RENESAS Package code: PRSS0003AG-A (Package name: TO-220FP) Ordering code #BB0</p>  <p><b>EOL announced</b></p>	<p>RENESAS Package code: PRSS0003AP-A (Package name: TO-220FPA) Ordering code #BG0</p> 	 <p>1. T<sub>1</sub> Terminal 2. T<sub>2</sub> Terminal 3. Gate Terminal</p>
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## Application

Low inrush current AC load.

## Maximum Ratings

Parameter	Symbol	Voltage class		Unit
		12		
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600		V
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	700		V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_T (RMS)$	10	A	Commercial frequency, sine full wave 360°conduction, $T_c = 82^\circ\text{C}$
Surge on-state current	$I_{TSM}$	60	A	60 Hz sinewave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusion	$I^2t$	15	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60 Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	5	W	
Average gate power dissipation	$P_G (AV)$	0.5	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	$I_{GM}$	2	A	
Junction Temperature	$T_j$	-40 to +150	°C	
Storage temperature	$T_{stg}$	-40 to +150	°C	
Isolation voltage <sup>Note6</sup>	$V_{iso}$	2000	V	$T_a=25^\circ\text{C}$ , AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

## Electrical Characteristics

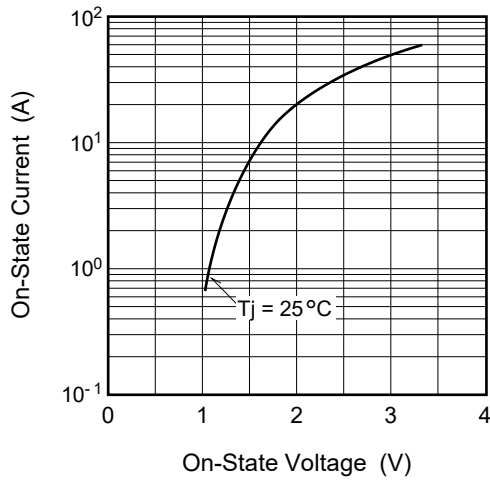
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	$I_{DRM}$	—	—	2.0	mA	$T_j = 125^\circ\text{C}$ , $V_{DRM}$ applied
On-state voltage	$V_{TM}$	—	—	1.8	V	$T_c = 25^\circ\text{C}$ , $I_{TM} = 15\text{ A}$ , instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGTI}$	—	—	1.5	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$V_{RGTI}$	—	—	1.5	
	III	$V_{RGTIII}$	—	—	1.5	
Gate trigger current <sup>Note2</sup>	I	$I_{FGTI}$	—	—	50	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$I_{RGTI}$	—	—	50	
	III	$I_{RGTIII}$	—	—	50	
Gate non-trigger voltage	$V_{GD}$	0.2	—	—	V	$T_j = 125^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	4.6	$^\circ\text{C/W}$	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutation voltage <sup>Note4</sup>	$(dv/dt)_c$	10	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}$

- Notes: 2. Measurement using the gate trigger characteristics measurement circuit.  
 3. The contact thermal resistance  $R_{th(c-f)}$  in case of greasing is  $0.5^\circ\text{C/W}$ .  
 4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.  
 5. Make sure that your finished product containing this device meets your safe isolation requirements.  
 For safety, it's advisable that heatsink is electrically floating.

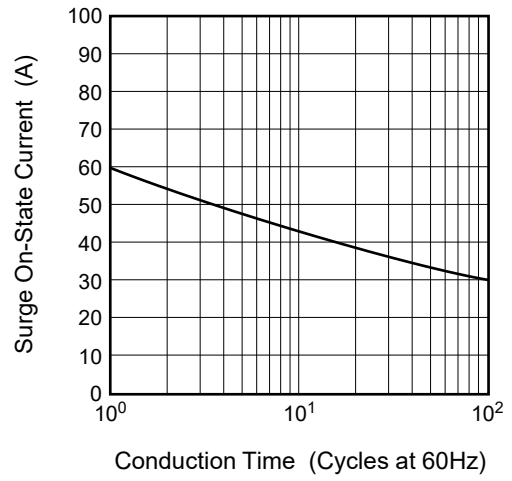
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -5\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	

Performance Curves

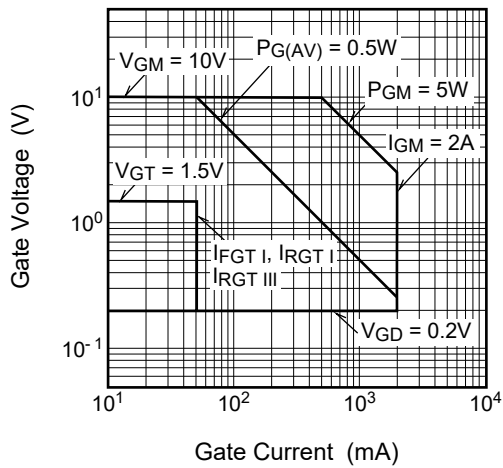
Maximum On-State Characteristics



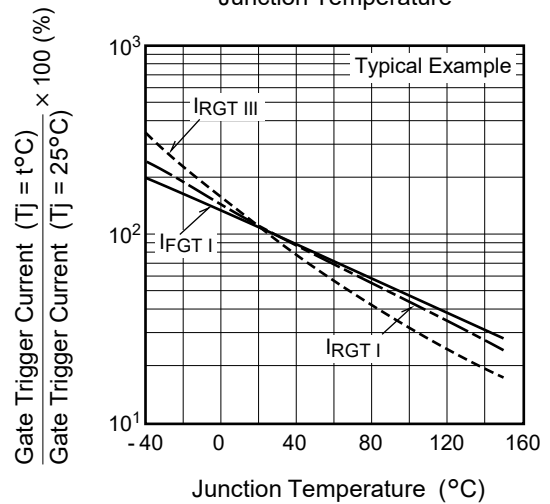
Rated Surge On-State Current



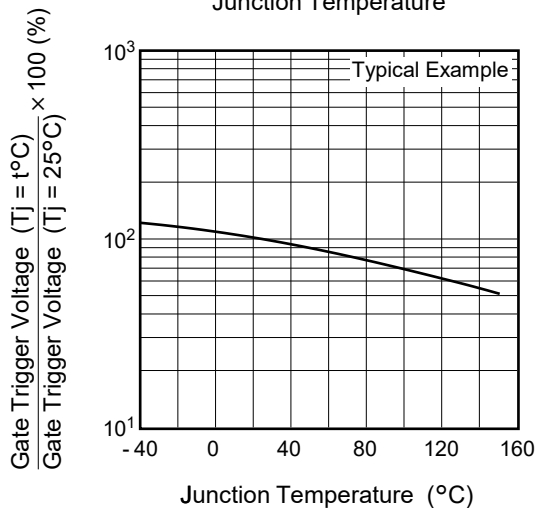
Gate Characteristics (I, II and III)



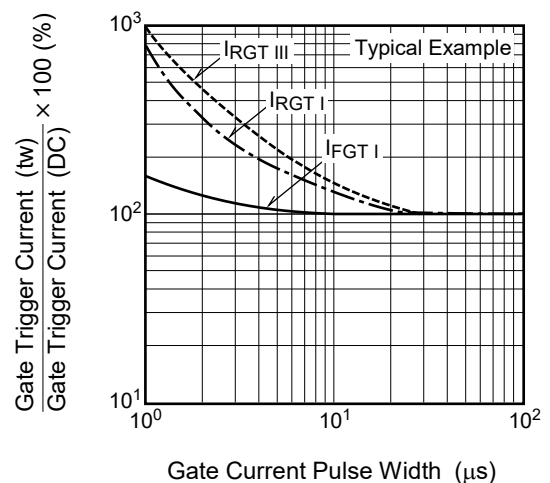
Gate Trigger Current vs. Junction Temperature

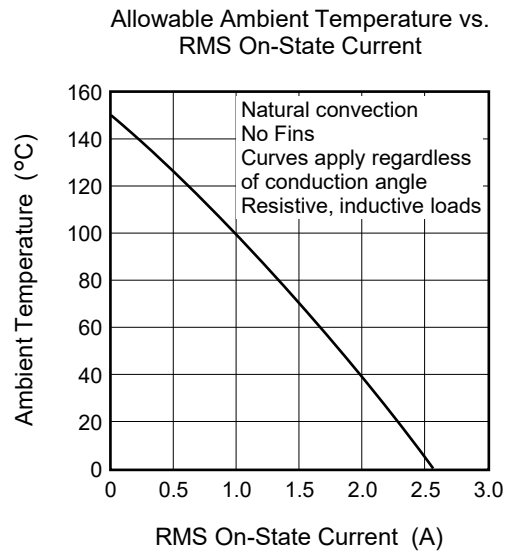
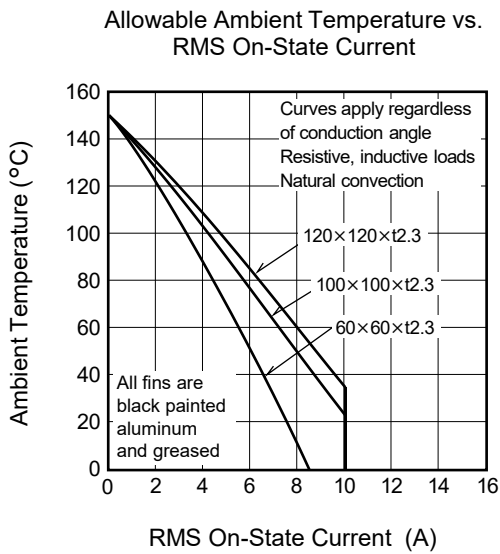
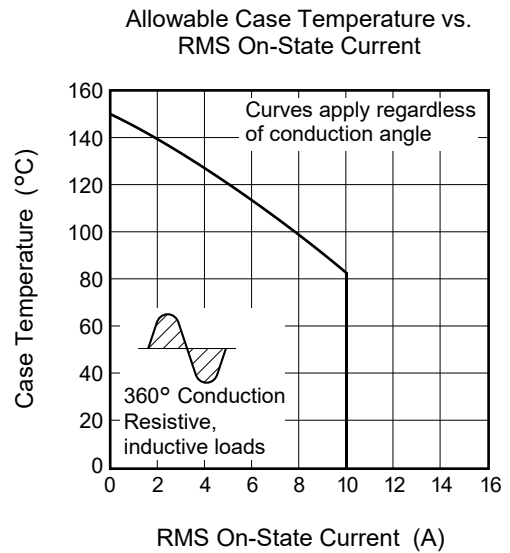
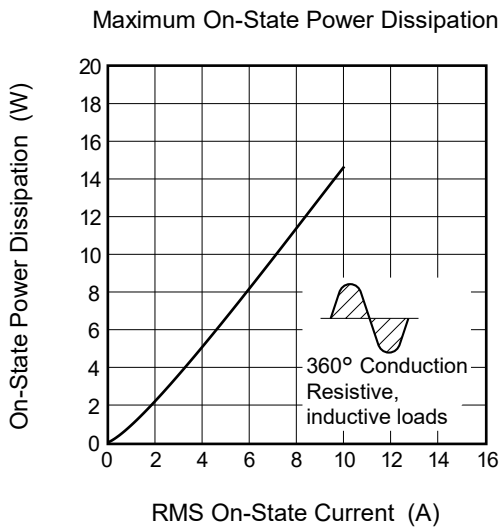
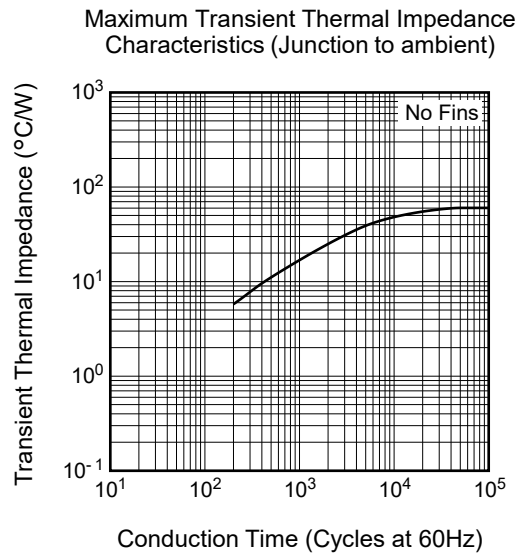
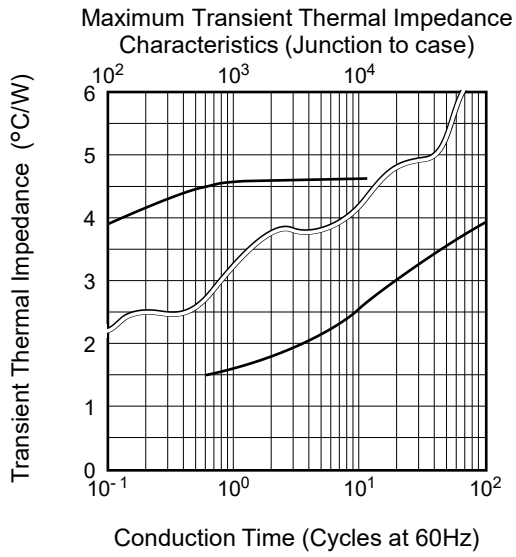


Gate Trigger Voltage vs. Junction Temperature

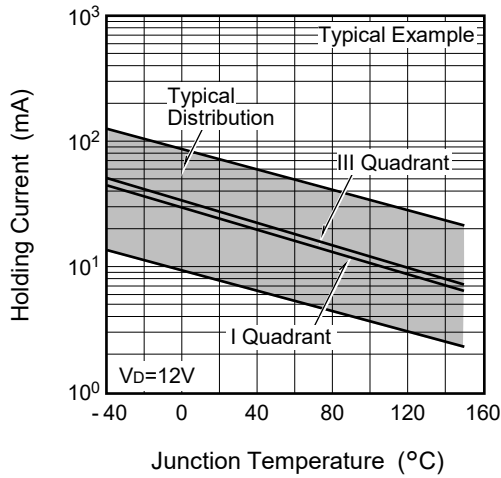


Gate Trigger Current vs. Gate Current Pulse Width

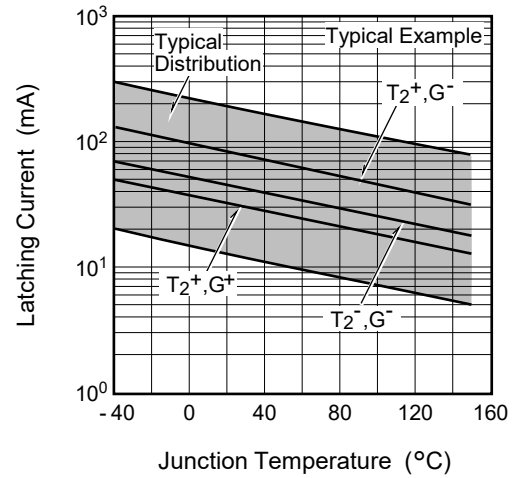




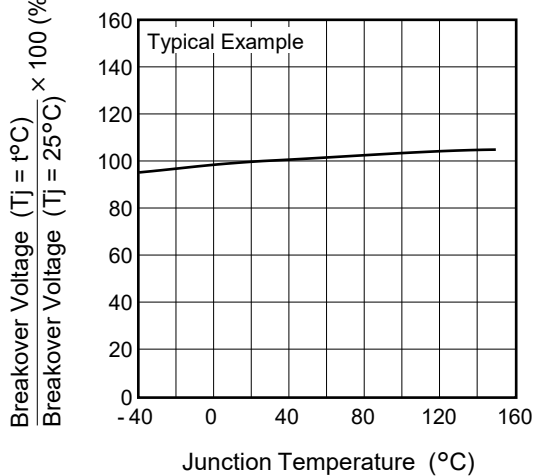
Holding Current vs. Junction Temperature



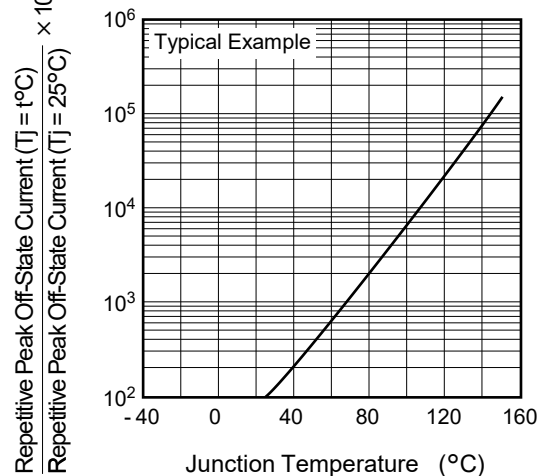
Latching Current vs. Junction Temperature



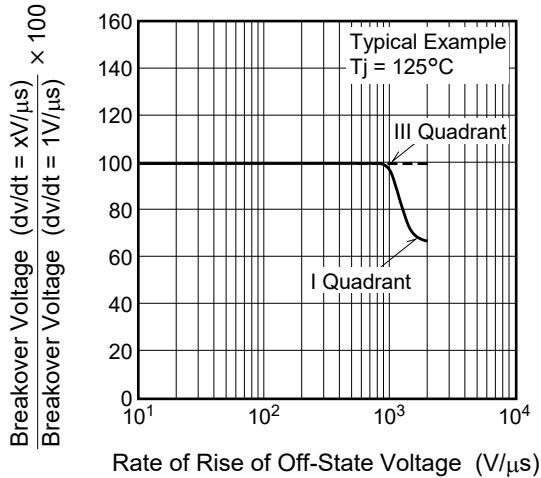
Breakover Voltage vs. Junction Temperature



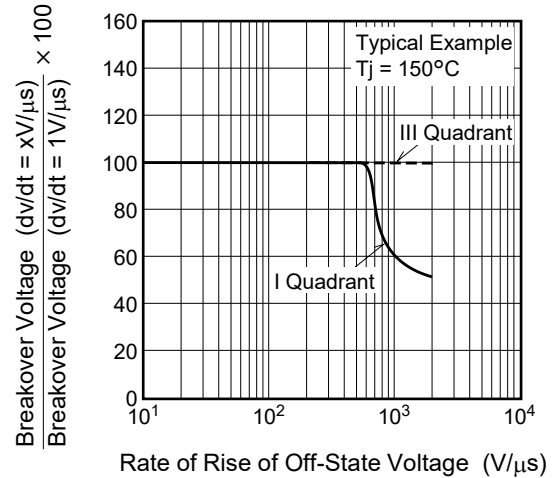
Repetitive Peak Off-State Current vs. Junction Temperature

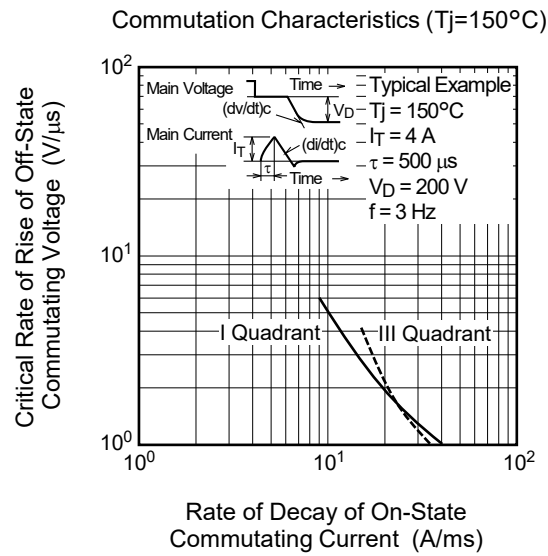
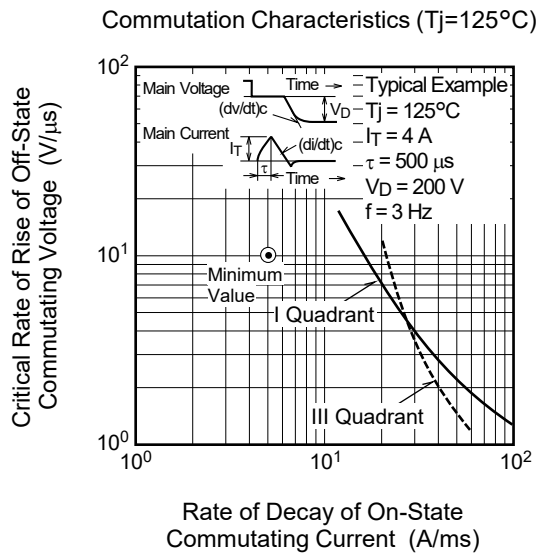


Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj=125°C)

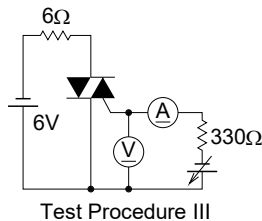
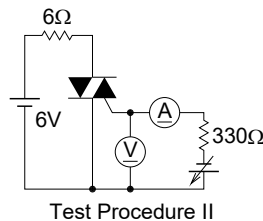
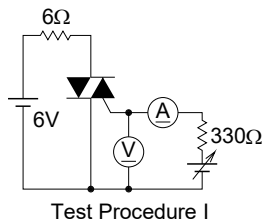


Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj=150°C)

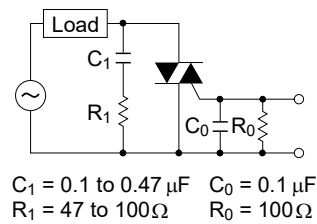




Gate Trigger Characteristics Test Circuits



Recommended peripheral components for Triac

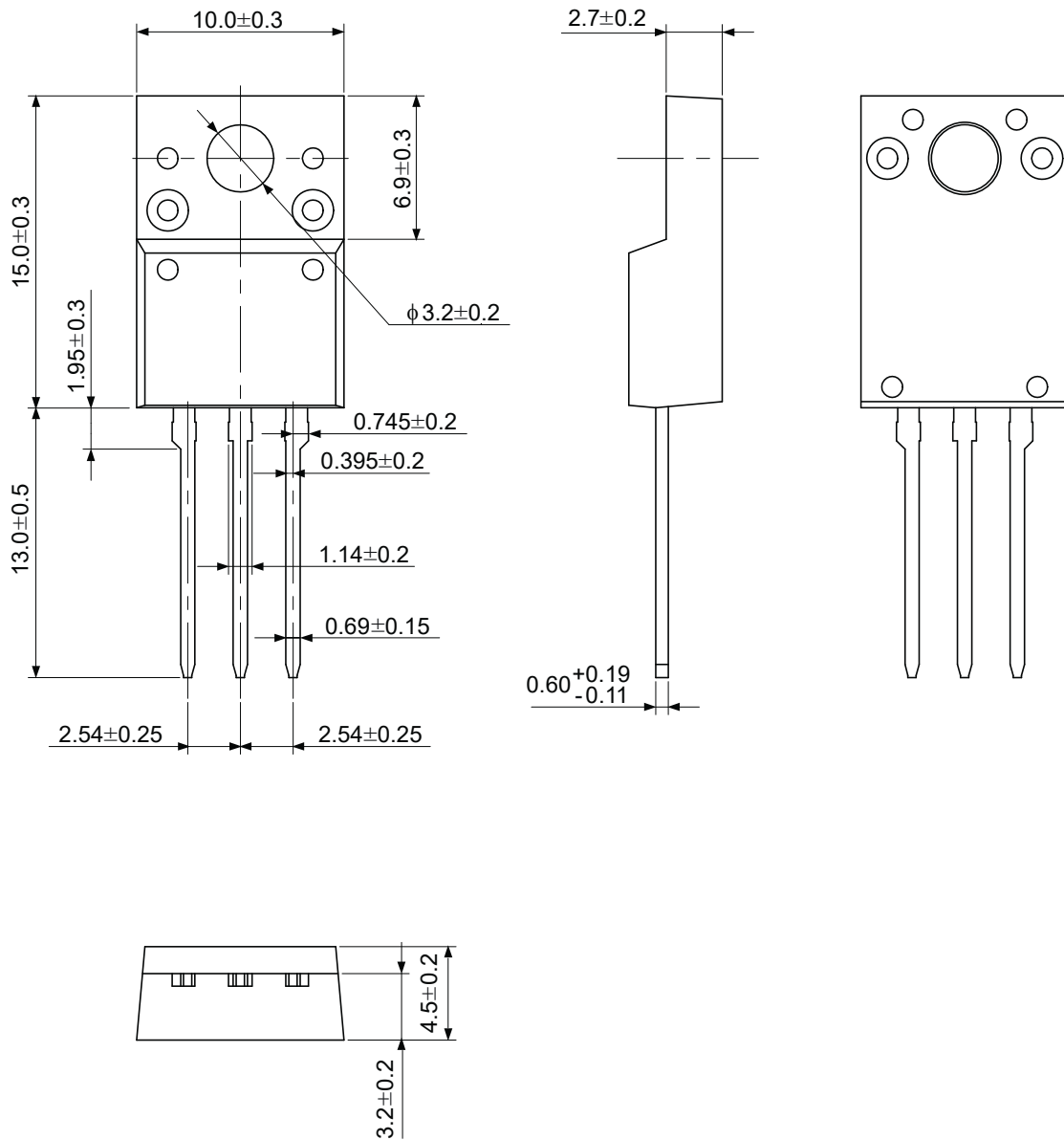


### Package Dimensions

Ordering code: #BG0

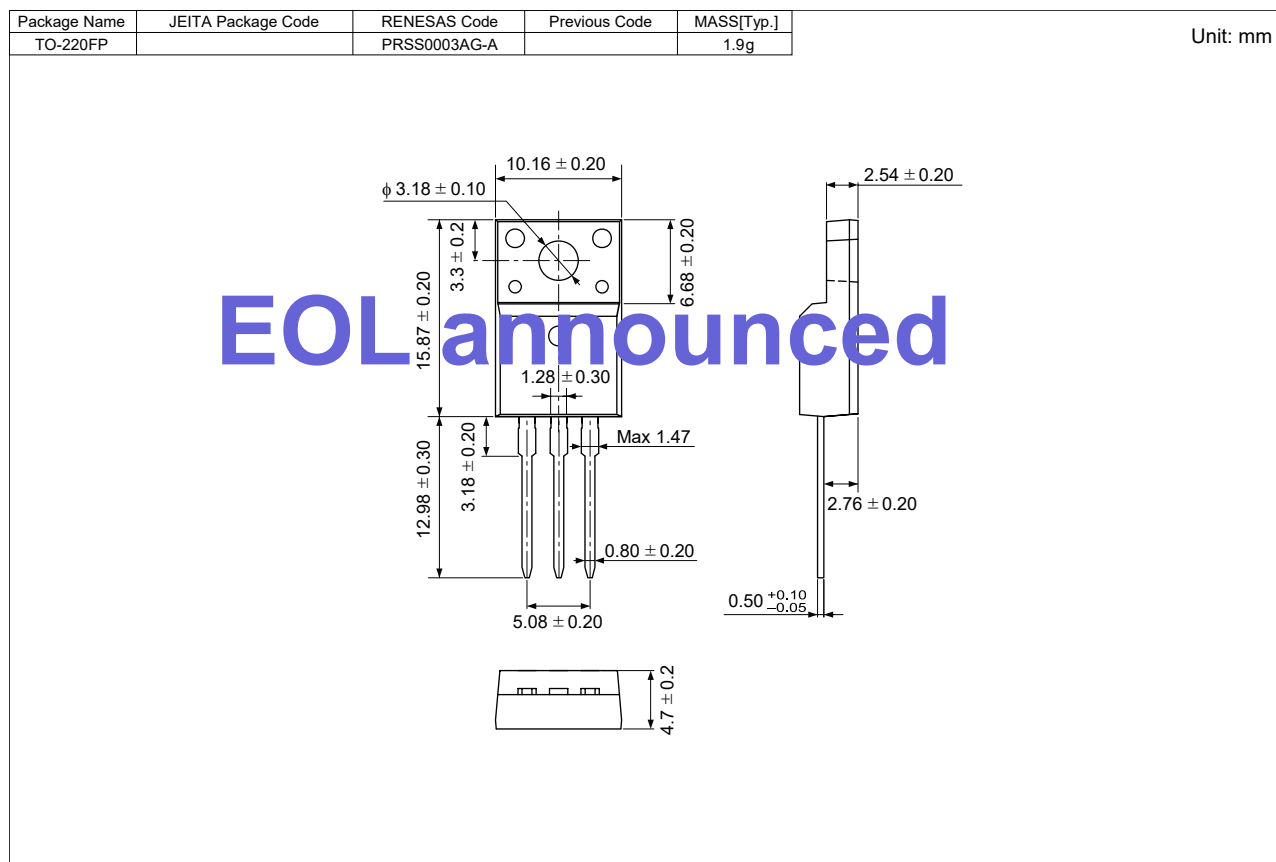
JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
-	PRSS0003AP-A	TO-220FPA	1.65

Unit: mm



## Package Dimensions

Ordering code: #BB0 <EOL announced>



## Ordering Information

Orderable Part Number	Package	Quantity <sup>Note6</sup>	Remark	Status
BCR10FM-12LC#BG0	TO-220FPA	50 pcs./ tube	Straight type	Mass Production
BCR10FM-12LC□□#BG0	TO-220FPA	50 pcs./ tube	□□:Lead form type	
BCR10FM-12LC#BB0	TO-220FP	50 pcs./ tube	Straight type	EOL announced
BCR10FM-12LC□□#BB0	TO-220FP	50 pcs./ tube	□□:Lead form type	

Notes: 6. Please confirm the specification about the shipping in detail.



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